

Fig.1

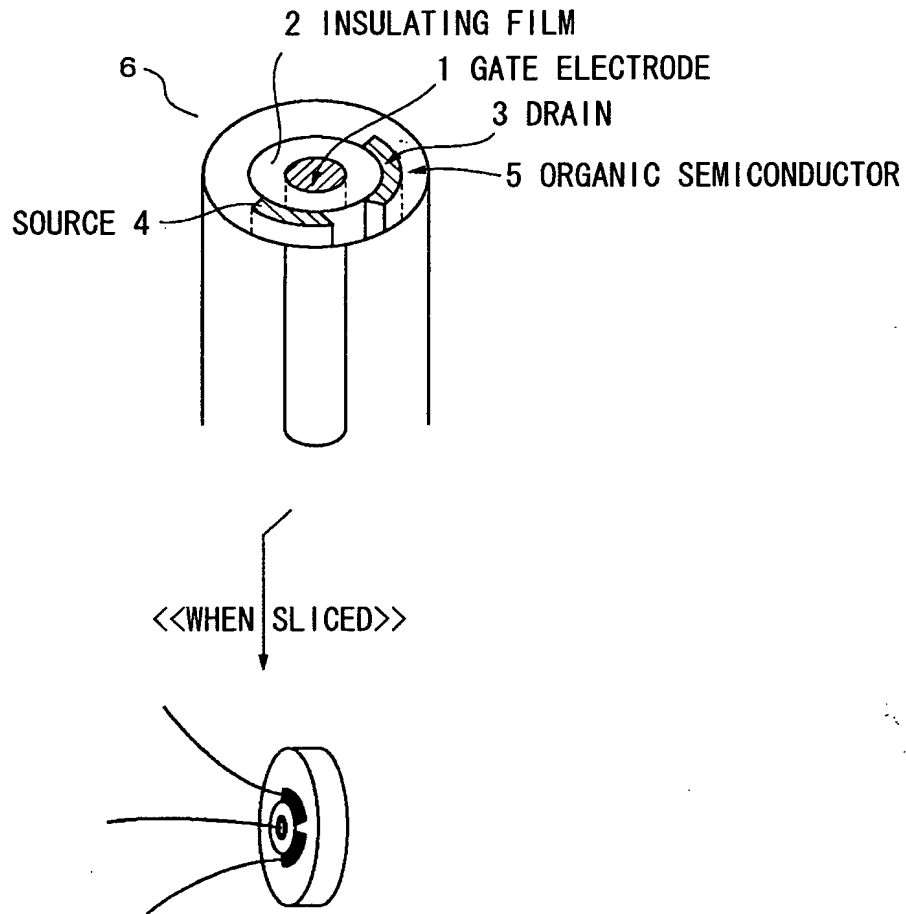


Fig.2

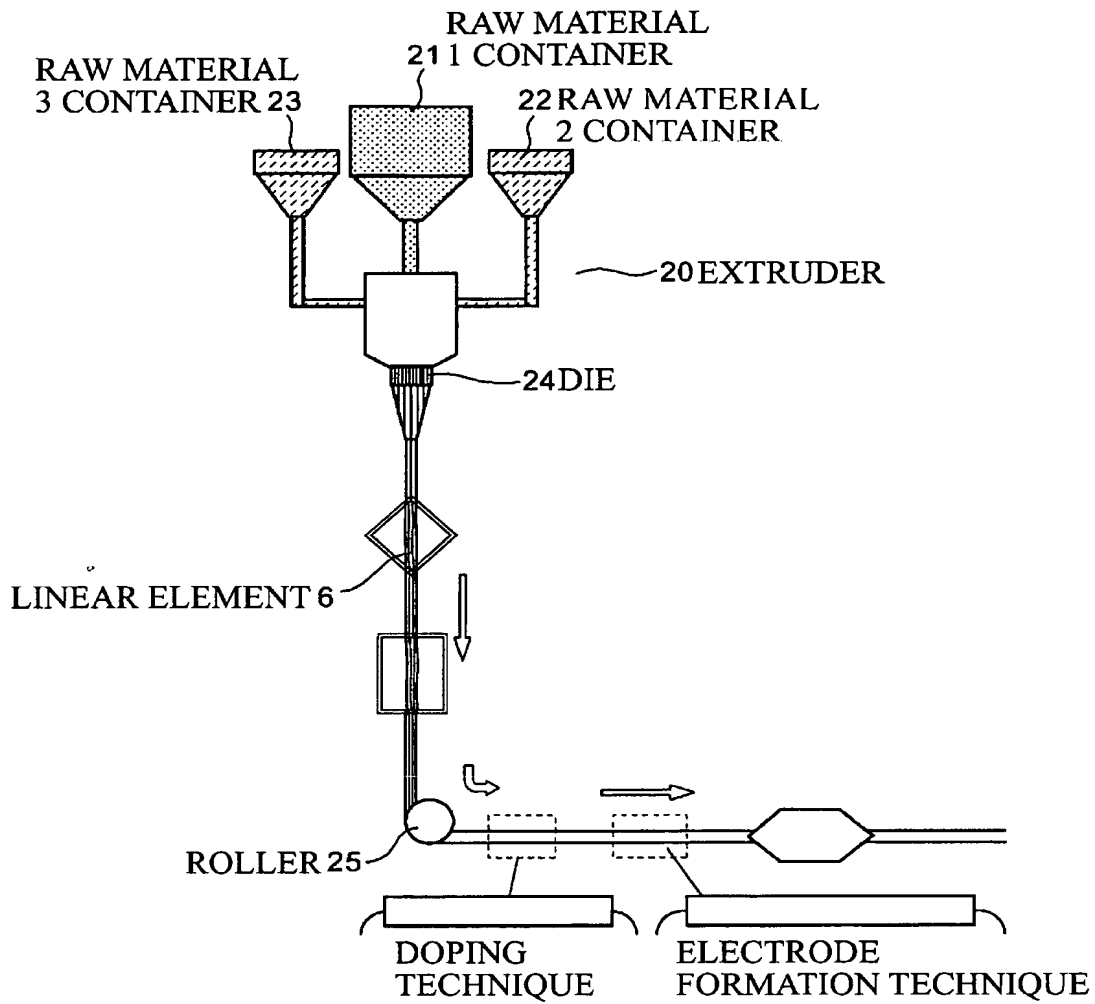


Fig.3

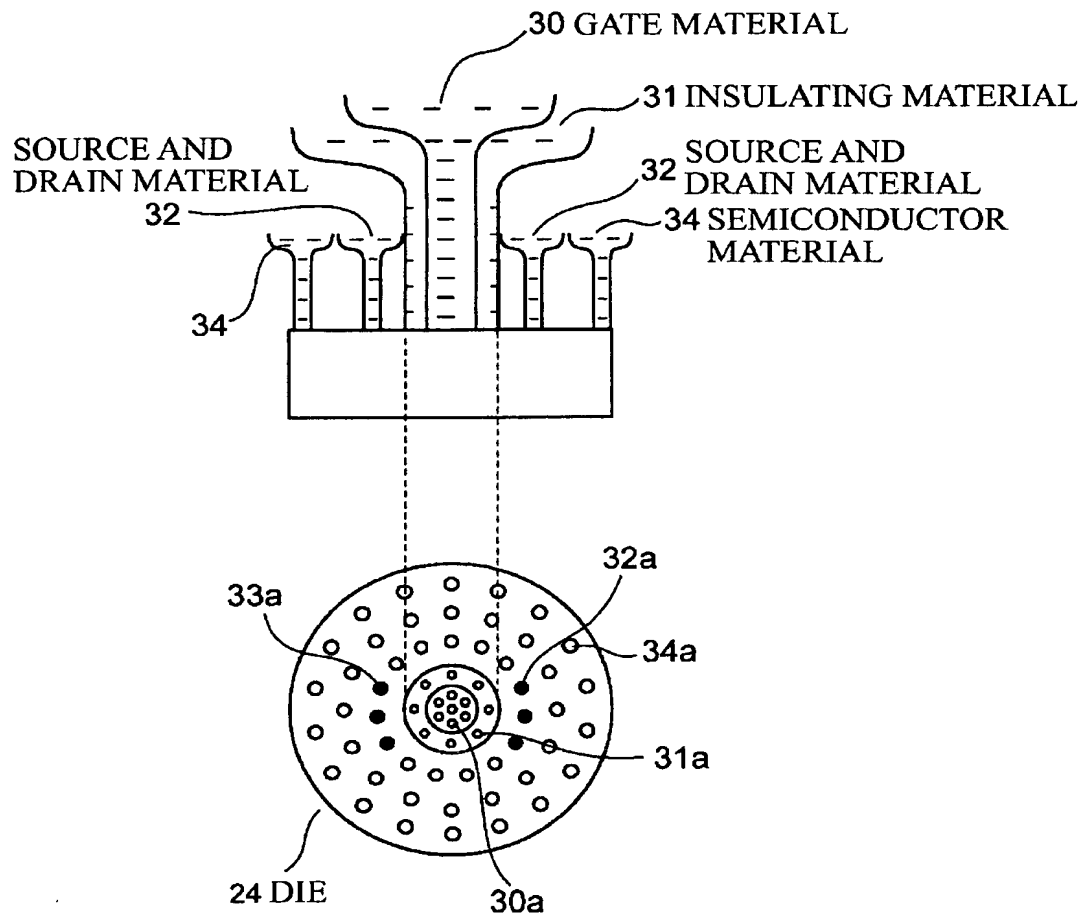
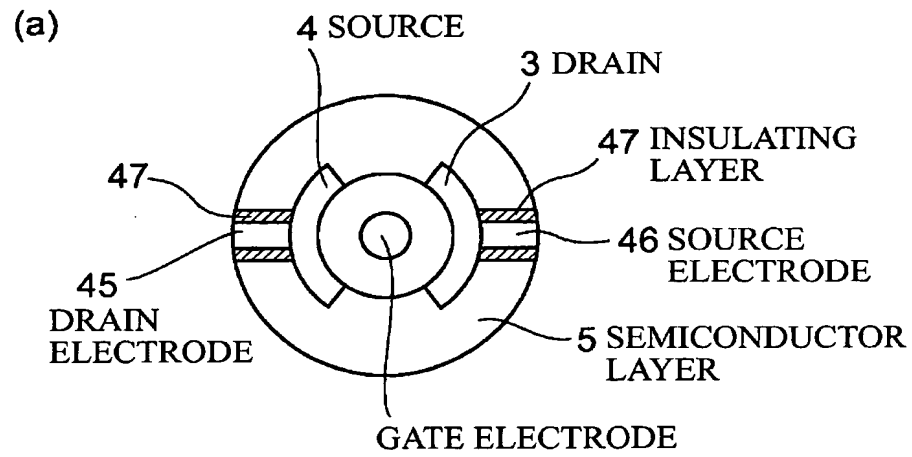


Fig.4



(b)

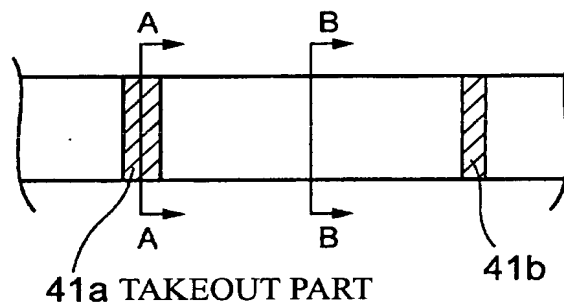


Fig.5

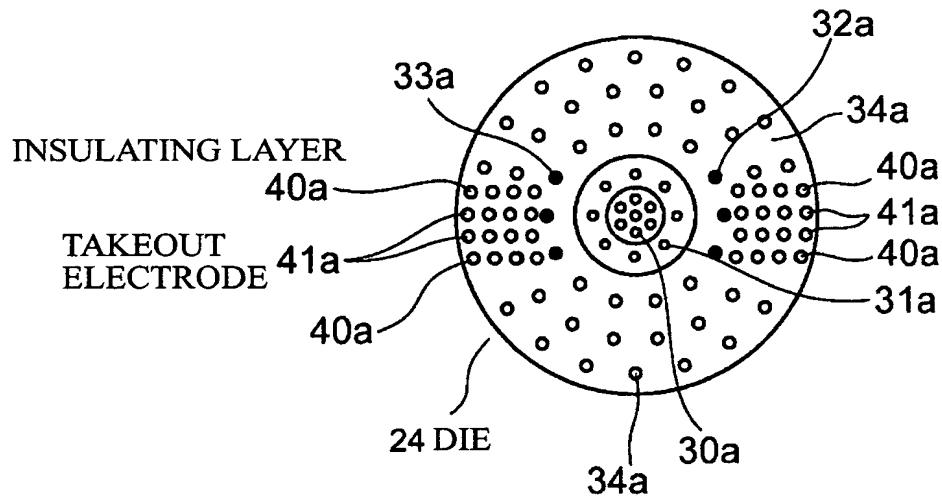


Fig.6

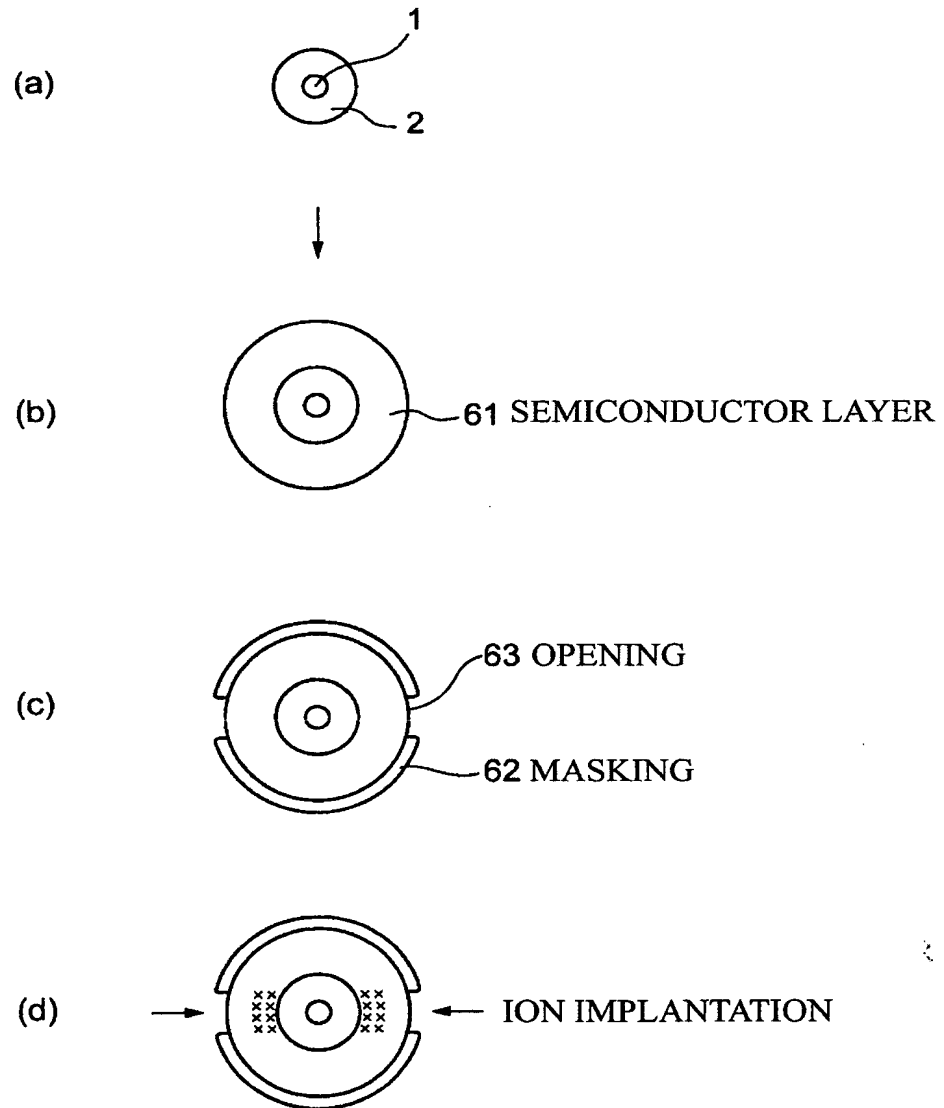


Fig.7

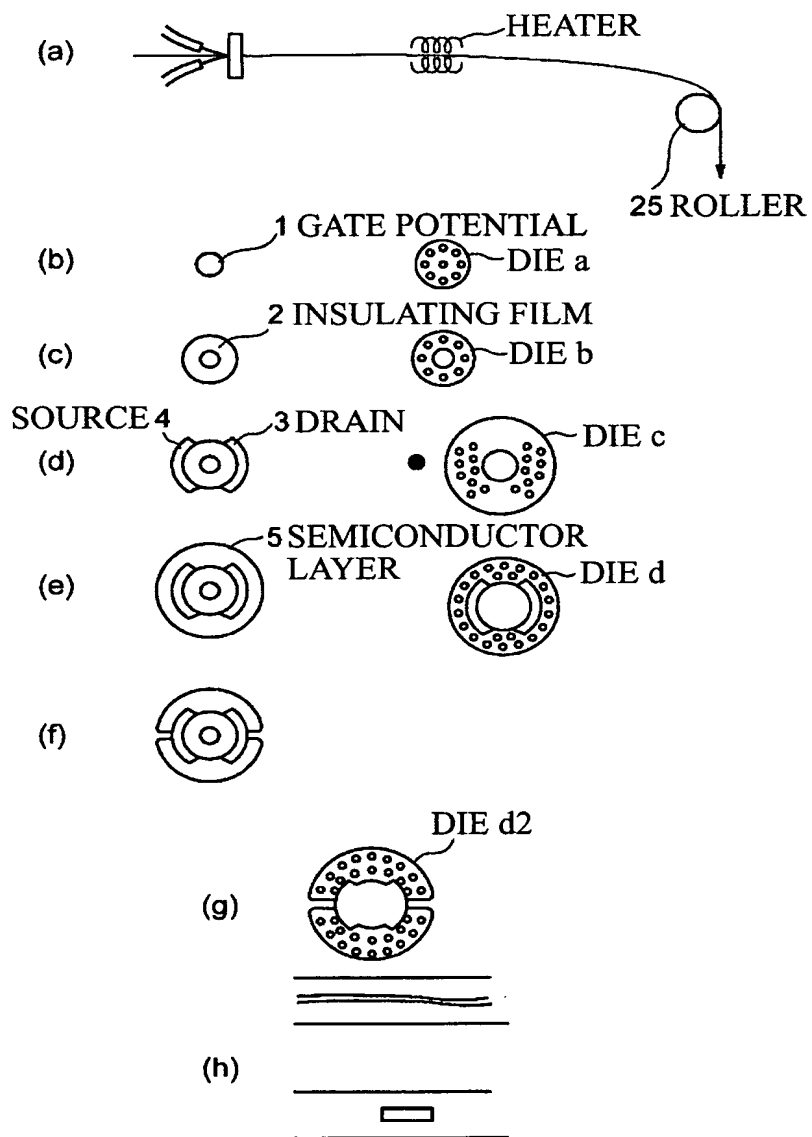
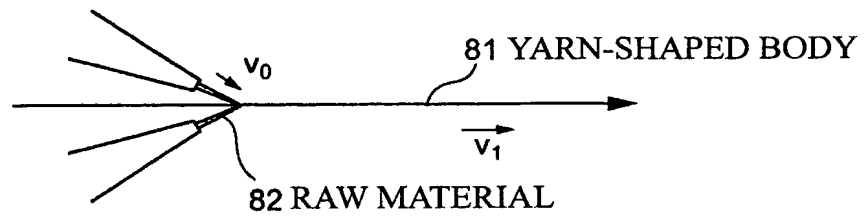


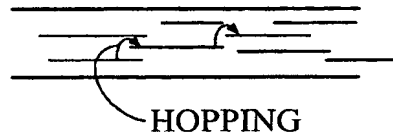
Fig.8

(a)

v_0 : RAW MATERIAL EJECTION SPEED
 v_1 : YARN-SHAPED BODY TRAVEL SPEED



(b)



(c)



Fig.9

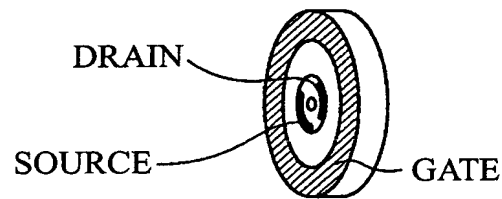
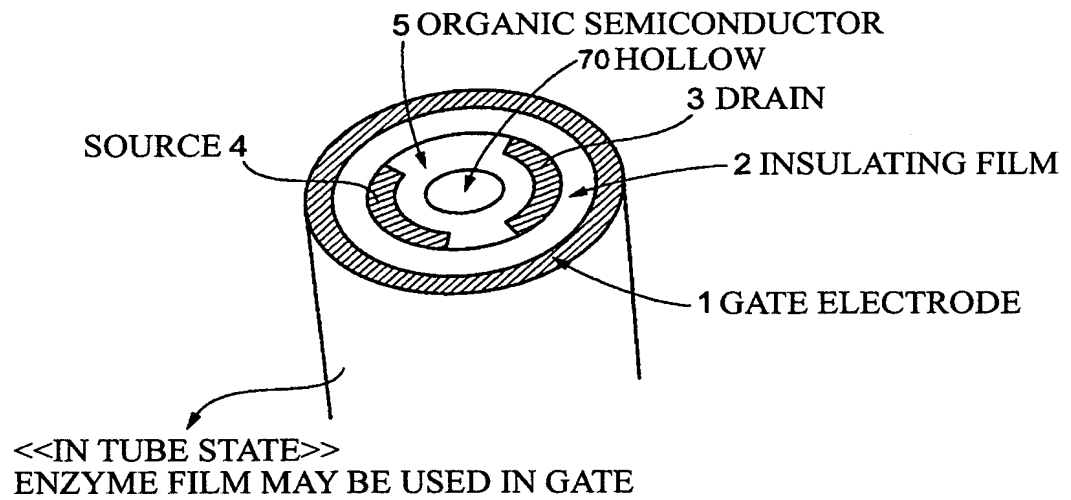


Fig.10

PHOTOVOLTAIC ELEMENT

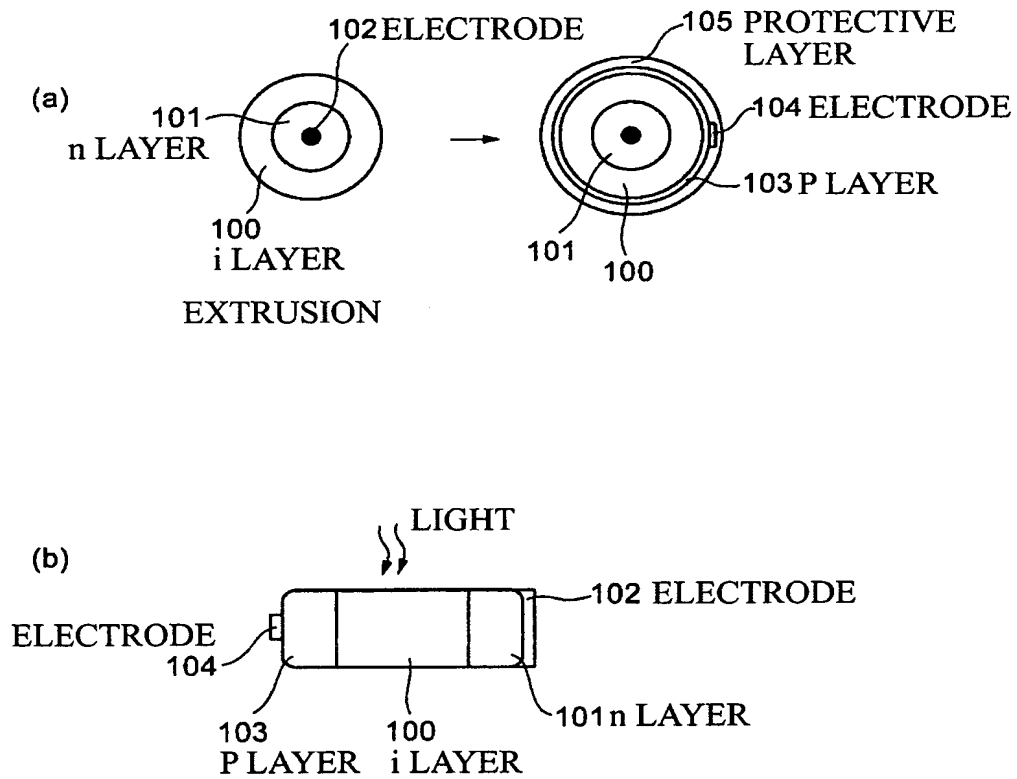


Fig.11

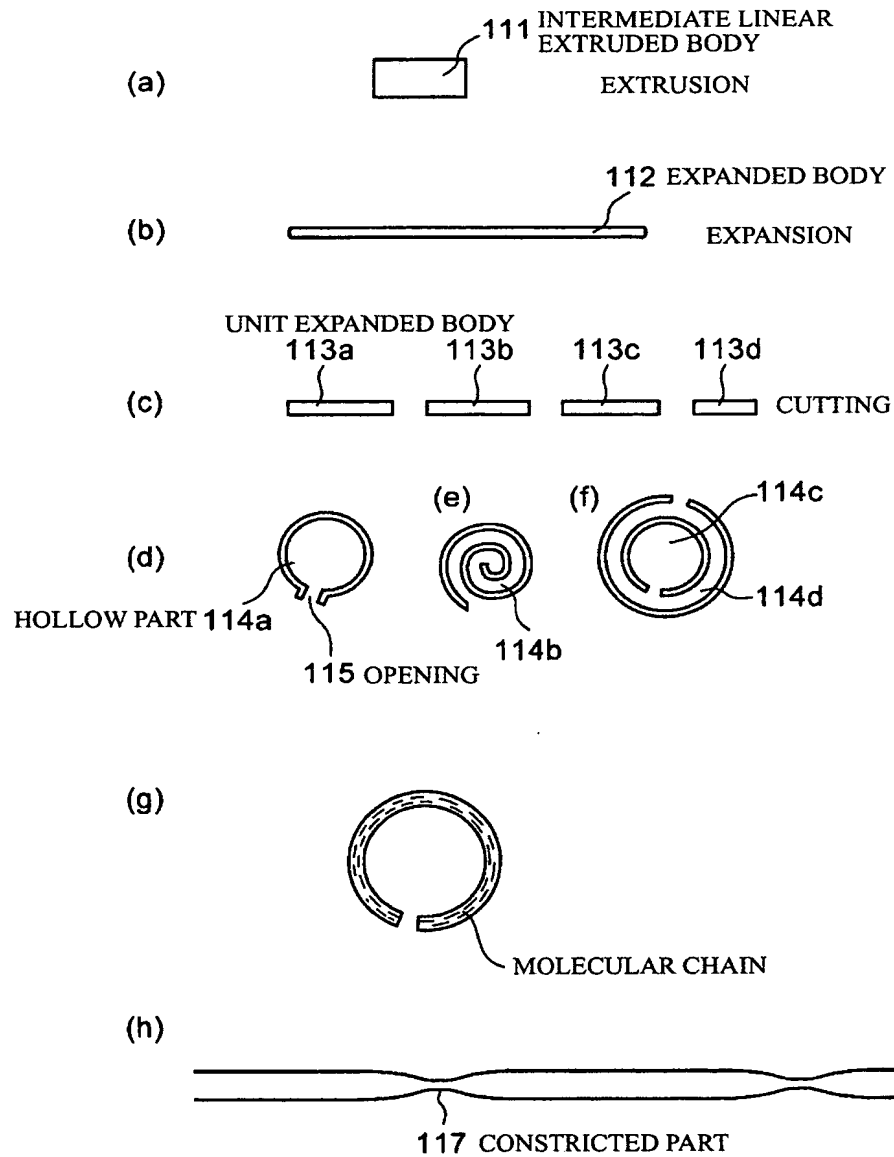


Fig.12

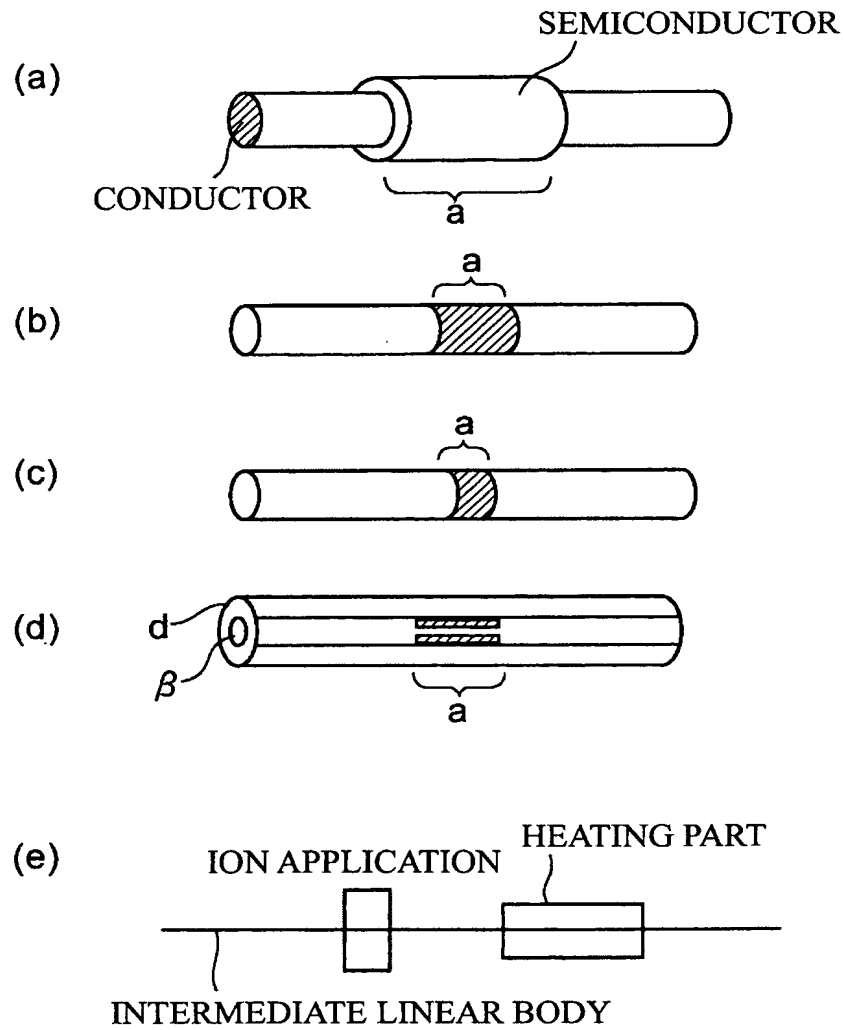


Fig.13

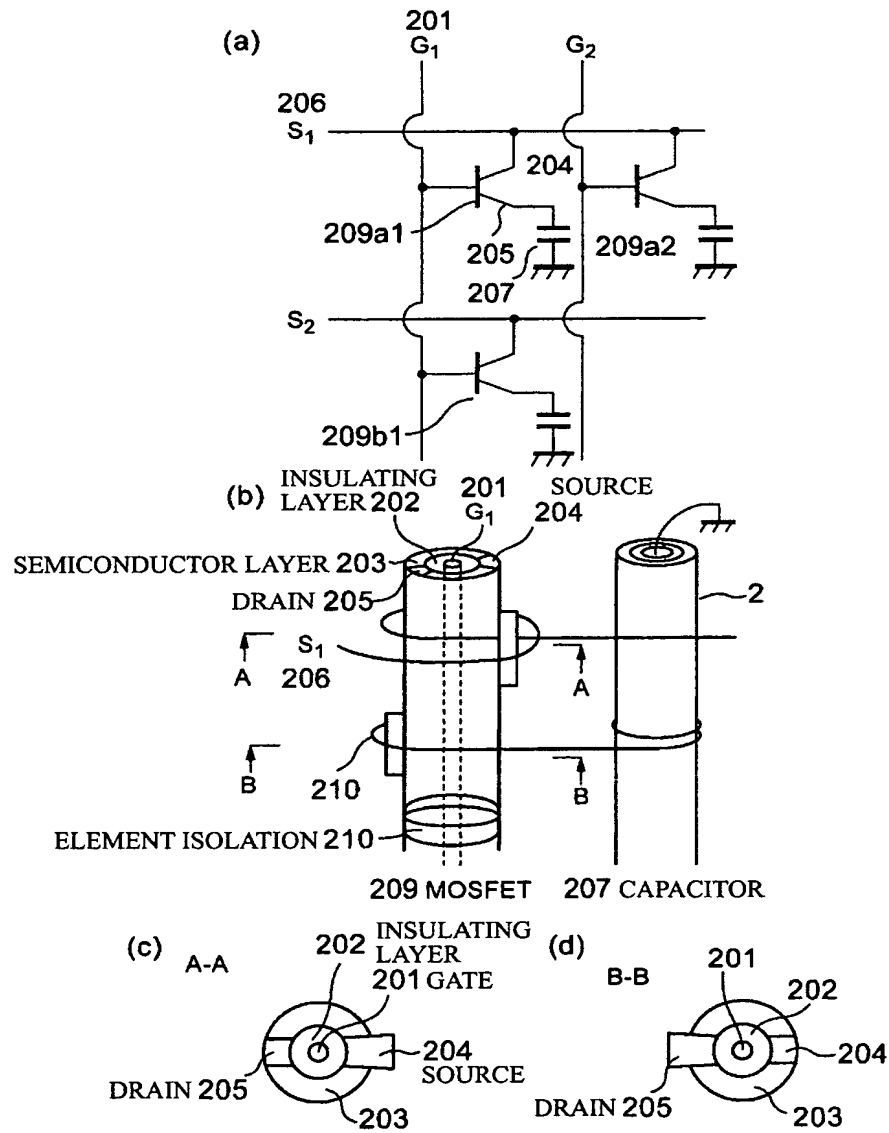


Fig.14

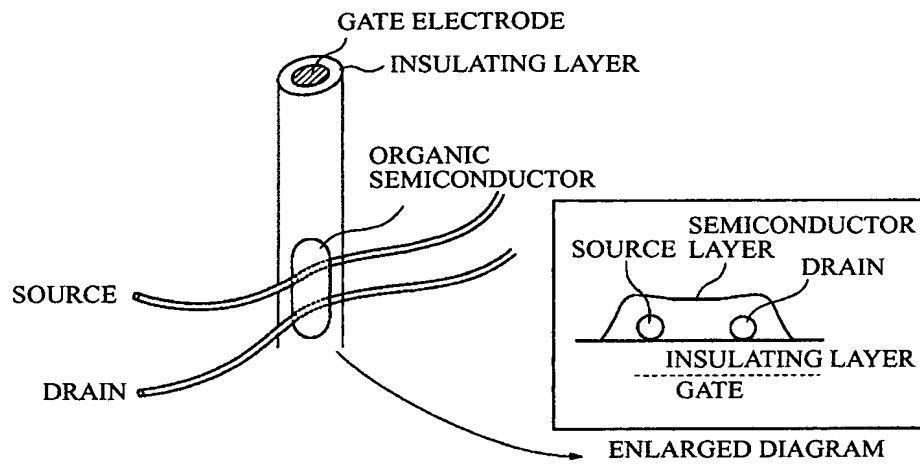


Fig.15

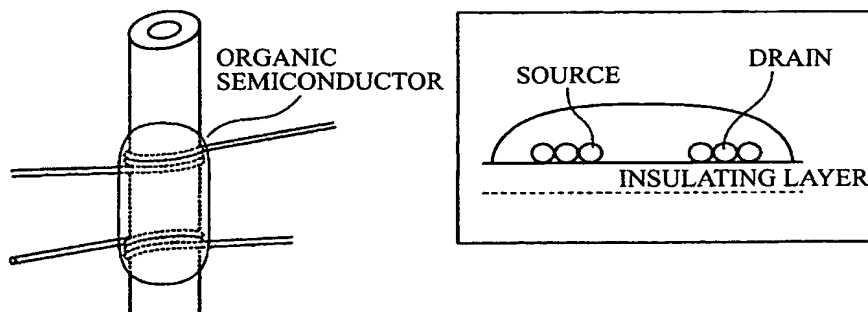


Fig.16

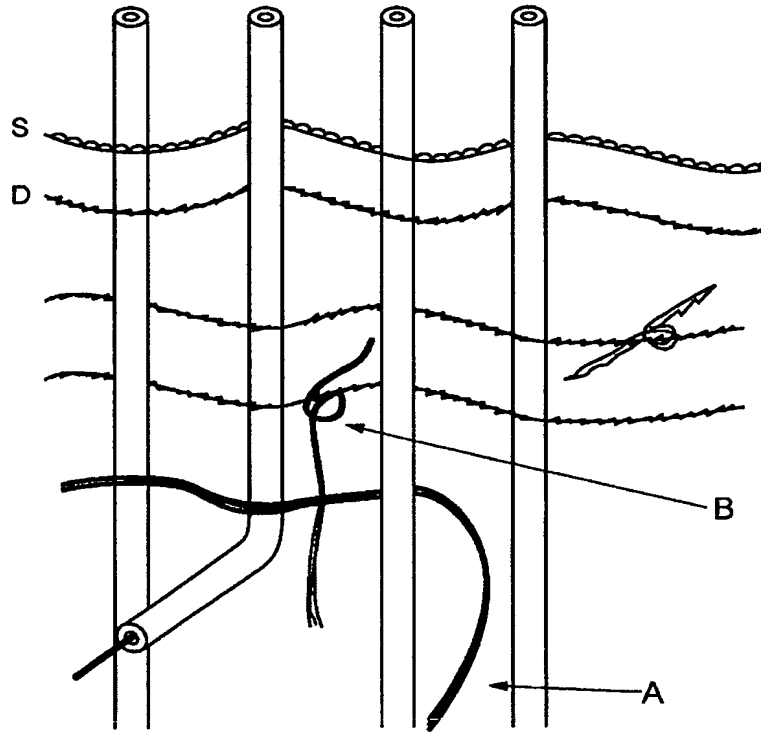


Fig.17

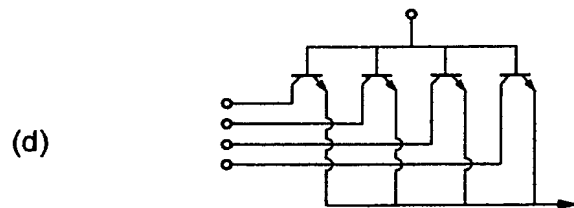
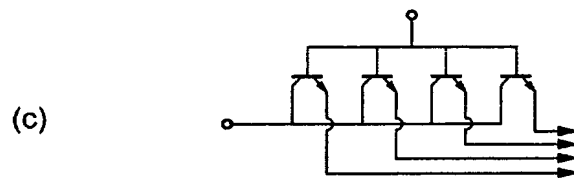
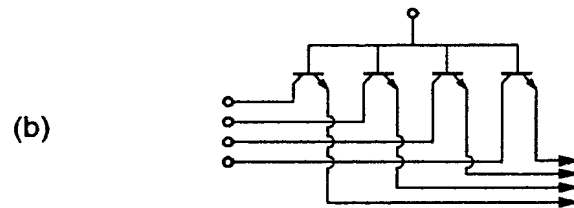
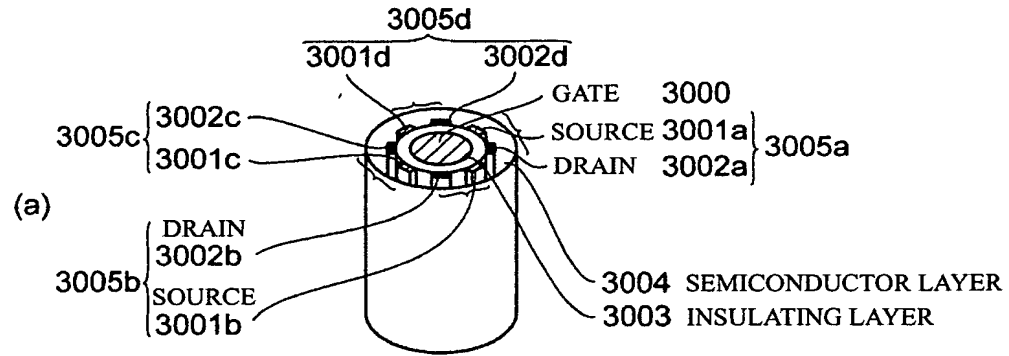


Fig.18

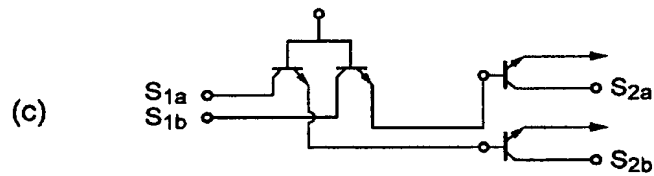
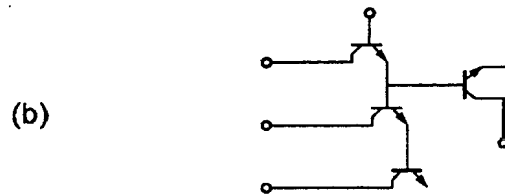
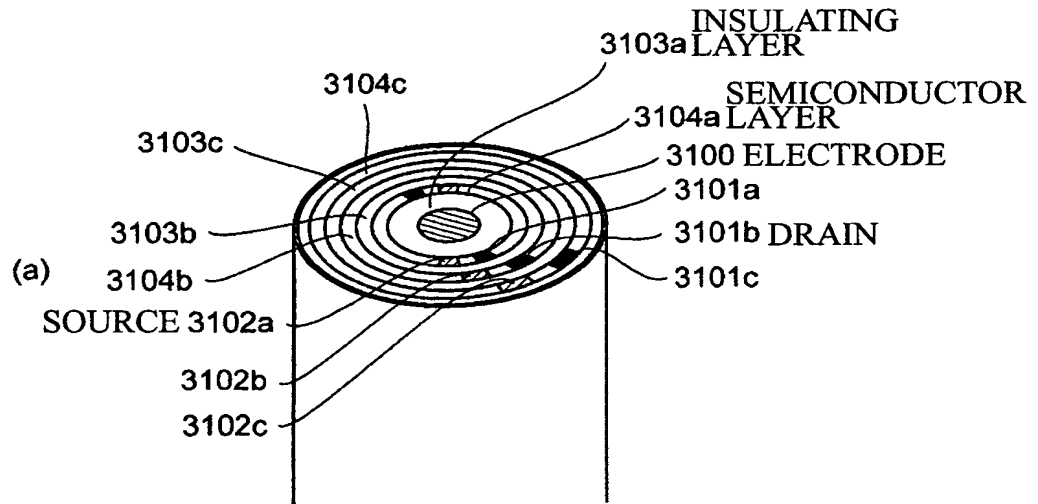
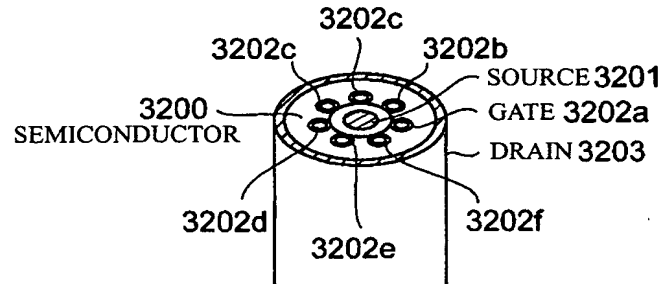
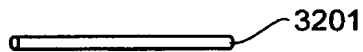


Fig.19



EXAMPLE OF PRODUCTION METHOD

① PREPARE SOURCE WIRING



② FORM SEMICONDUCTOR LAYER 1

COAT SILVER WIRE WITH SEMICONDUCTOR LAYER BY DIPPING METHOD



③ FORM GATE ELECTRODE



④ FORM SEMICONDUCTOR LAYER



⑤ FORM DRAIN ELECTRODE

FIG.20

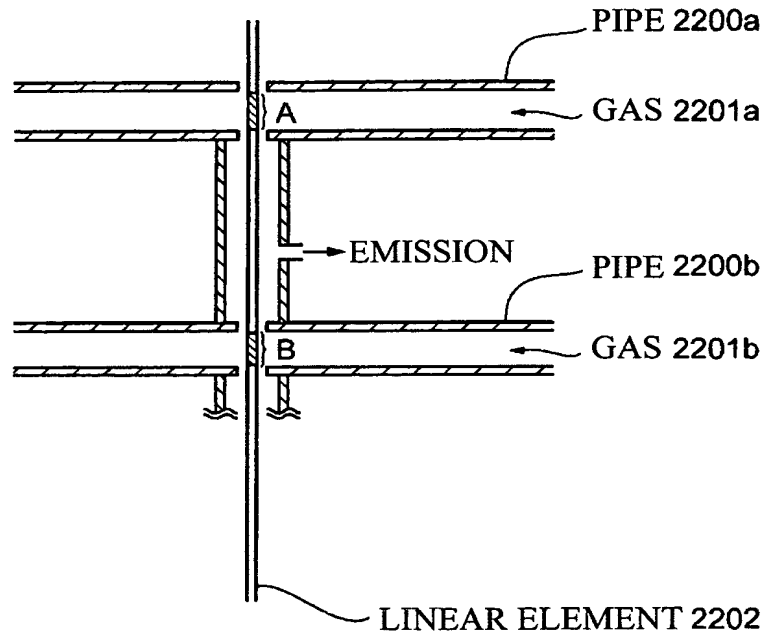


Fig.21

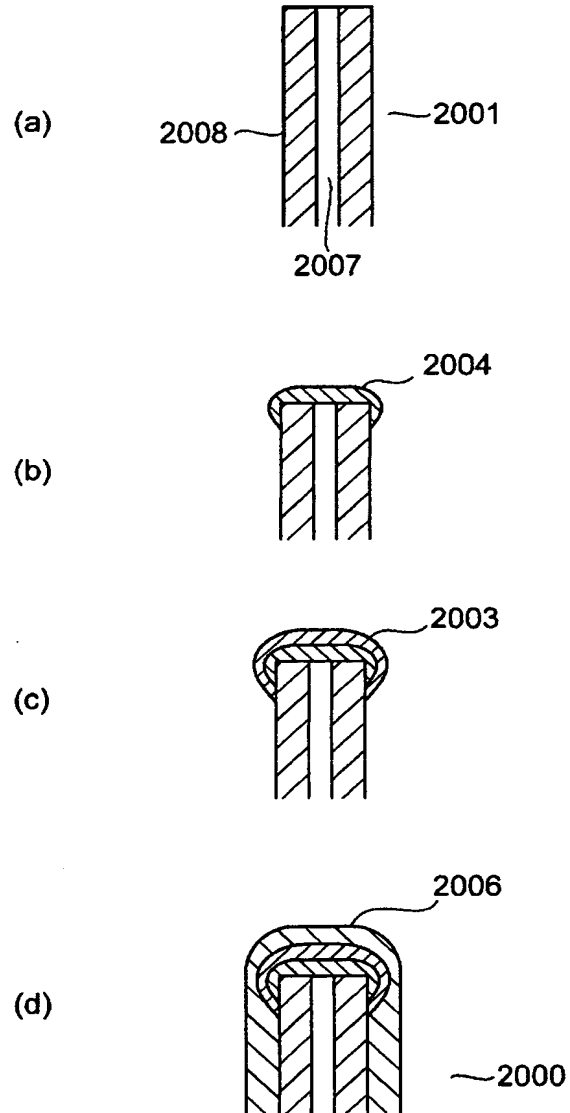


Fig.22

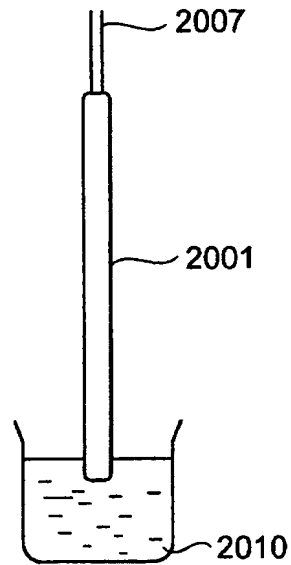


Fig.23

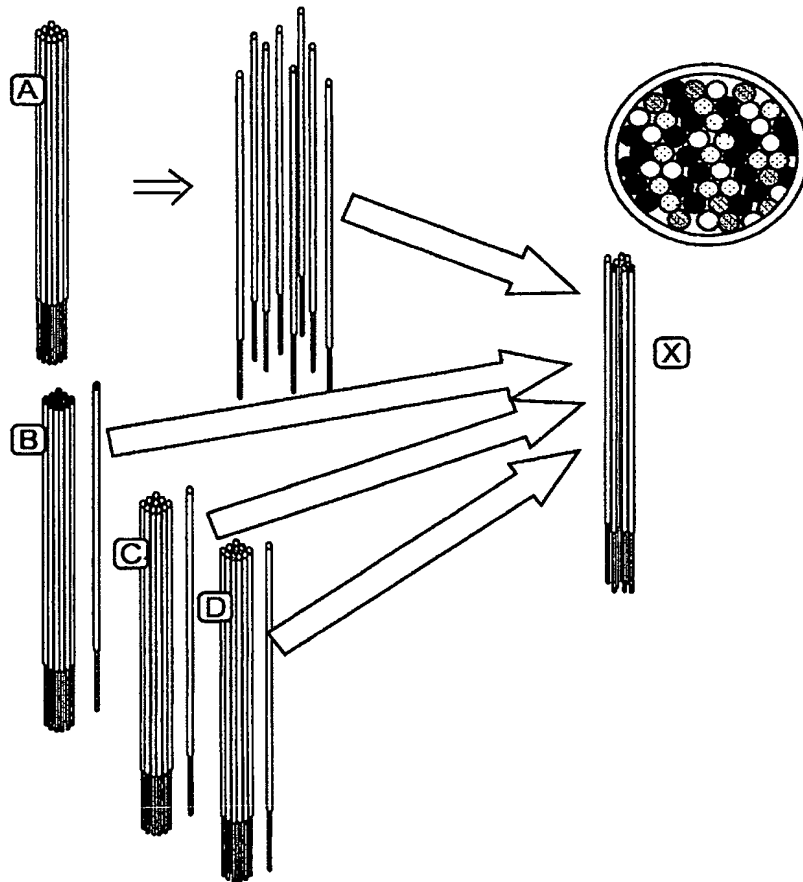


Fig.24

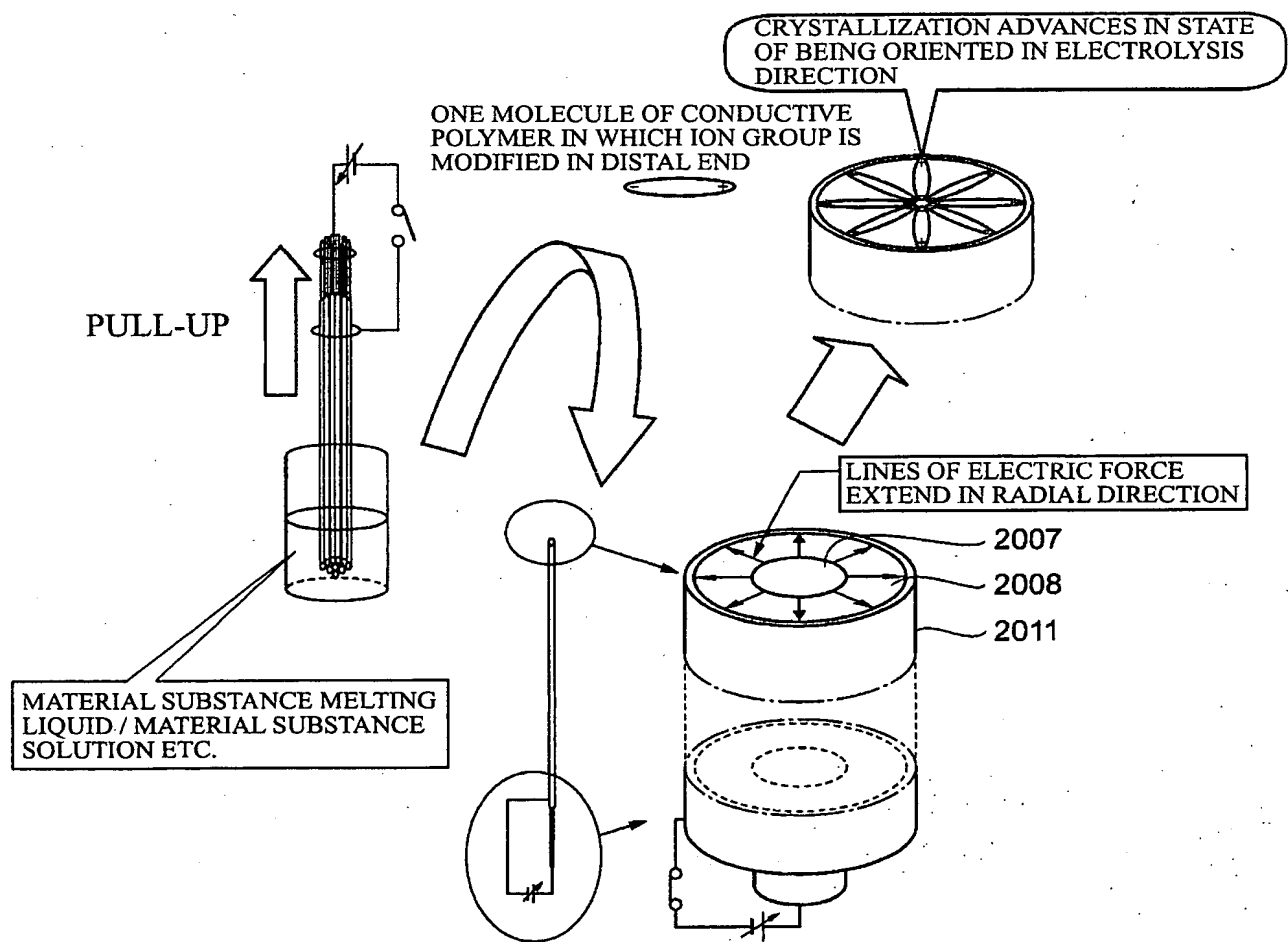


Fig.25

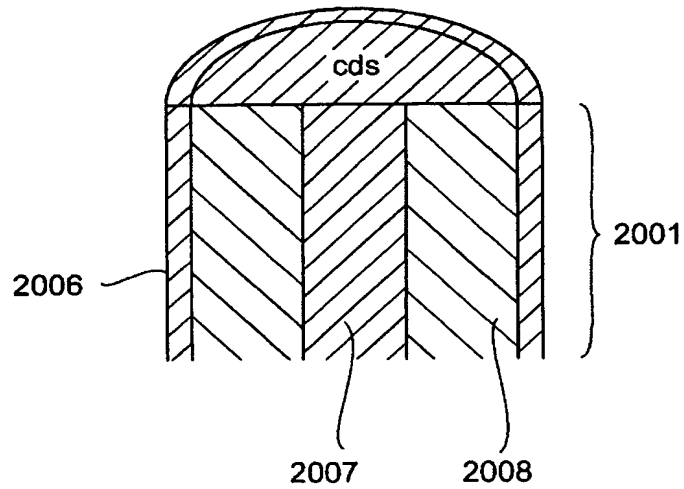


Fig.26

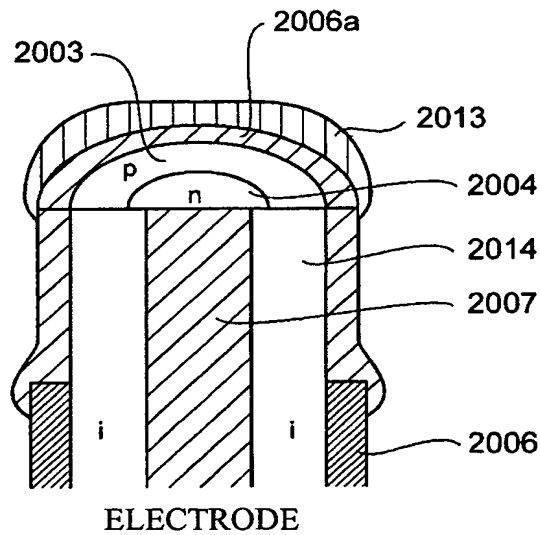


Fig.27

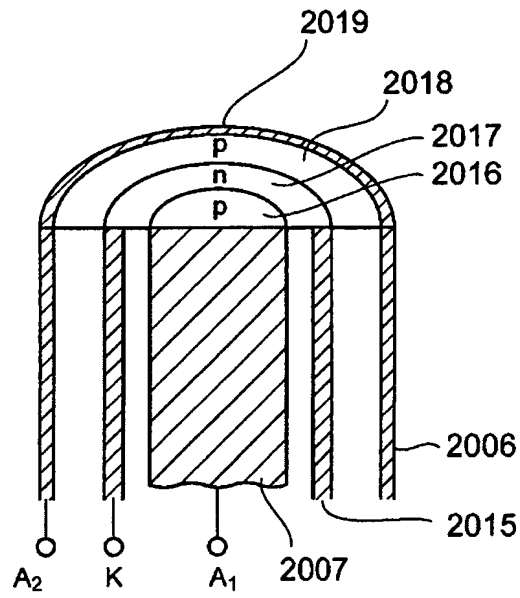


Fig.28

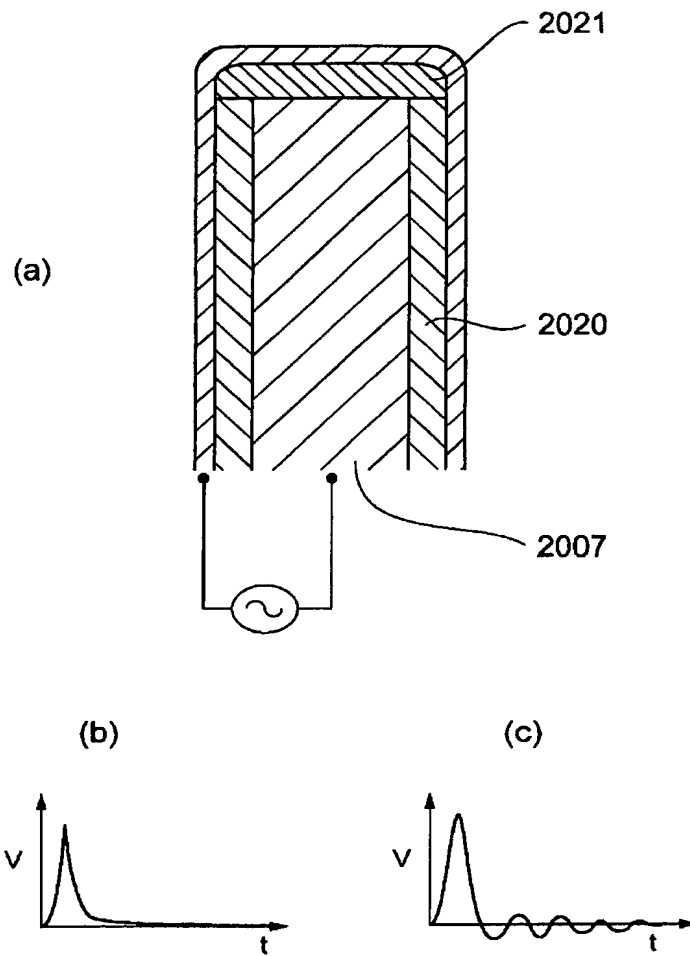


Fig.29

